MA3304V10000000

N-Ch and P-Ch 30V Fast Switching MOSFETs

General Description

The MA3304V is the highest performance trench N-ch and P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The MA3304V meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

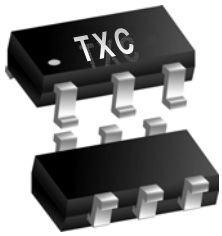
Green

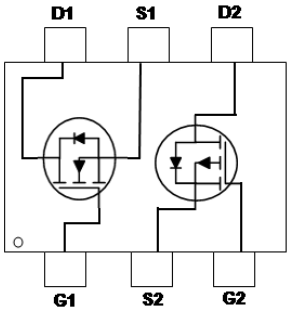
BVDSS	RDSON	ID
30V	55mΩ	3.7A
-30V	135mΩ	-2.5A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

TSOP6 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	3.7	-2.5	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ 10V[1]	3	-2	A
I_{DM}	Pulsed Drain Current[2]	7.4	-5	A
P_D@T_A=25°C	Total Power Dissipation[3]	1.5	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	110	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	70	°C/W

Rev A.01 D071510

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=1mA	---	0.016	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=3A	---	45	55	mΩ
		V_{GS}=4.5V , I_D=2A	---	60	75	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.04	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25°C	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55°C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=4A	---	8	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.3	4.6	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=3A	---	2.75	---	nC
Q_{gs}	Gate-Source Charge		---	0.67	---	
Q_{gd}	Gate-Drain Charge		---	1.52	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=4A	---	3.6	---	ns
T_r	Rise Time		---	14.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	11.5	---	
T_f	Fall Time		---	1.9	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	220	---	pF
C_{oss}	Output Capacitance		---	38	---	
C_{rss}	Reverse Transfer Capacitance		---	32	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	3.7	A
I_{SM}	Pulsed Source Current[2,4]		---	---	7.4	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150°C junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , I_D=-1mA	---	-0.02	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-2A	---	110	135	mΩ
		V_{GS}=-4.5V , I_D=-1A	---	185	230	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.5	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.72	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25°C	---	---	1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55°C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-3A	---	3.8	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	26	52	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-1A	---	3.3	---	nC
Q_{gs}	Gate-Source Charge		---	0.88	---	
Q_{gd}	Gate-Drain Charge		---	1.55	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	9.6	---	ns
T_r	Rise Time		---	6.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	21.5	---	
T_f	Fall Time		---	3.3	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	203	---	pF
C_{oss}	Output Capacitance		---	42	---	
C_{rss}	Reverse Transfer Capacitance		---	34	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-2.5	A
I_{SM}	Pulsed Source Current[2,4]		---	---	-5	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25°C	---	---	-1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3The power dissipation is limited by 150°C junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

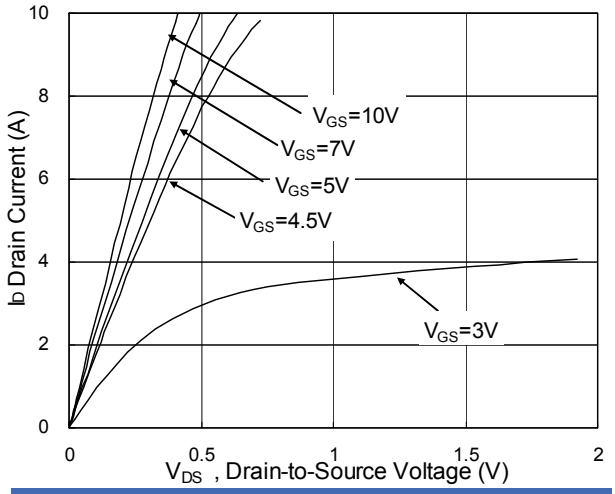


Fig.1 Typical Output Characteristics

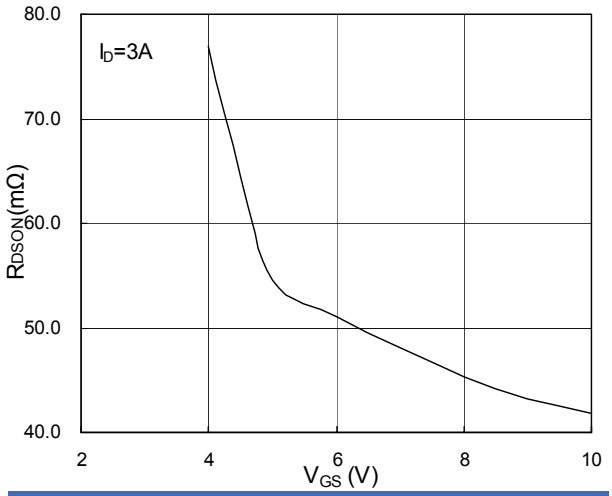


Fig.2 On-Resistance vs. G-S Voltage

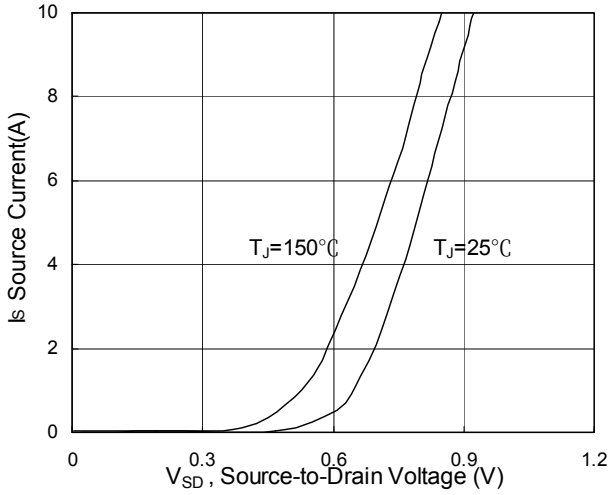


Fig.3 Forward Characteristics of Reverse

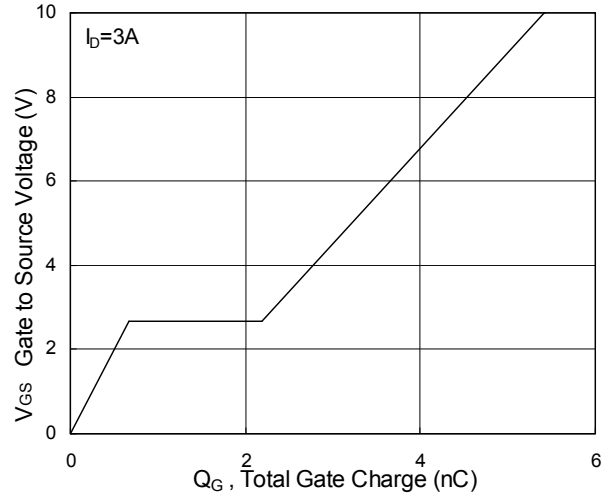


Fig.4 Gate-charge Characteristics

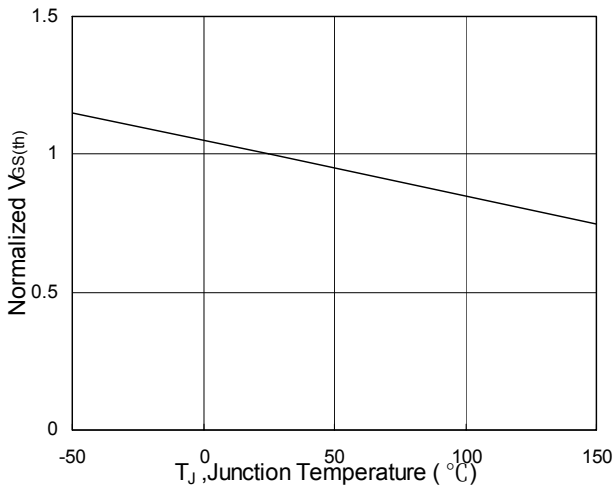


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

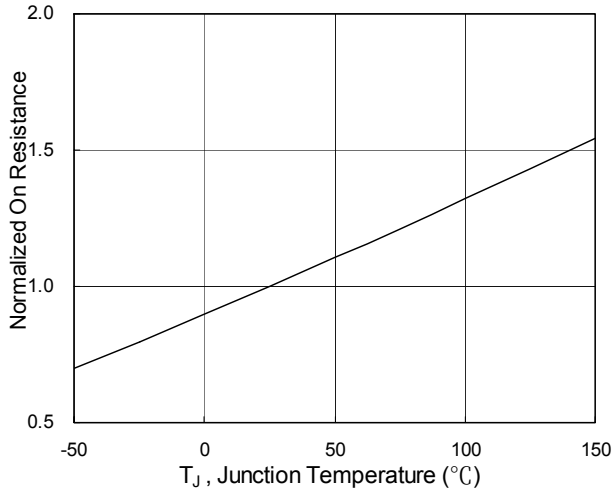


Fig.6 Normalized R_{DSON} vs. T_J

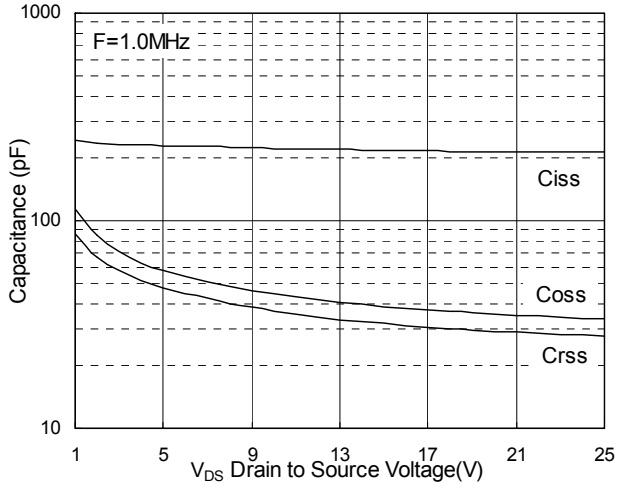


Fig.7 Capacitance

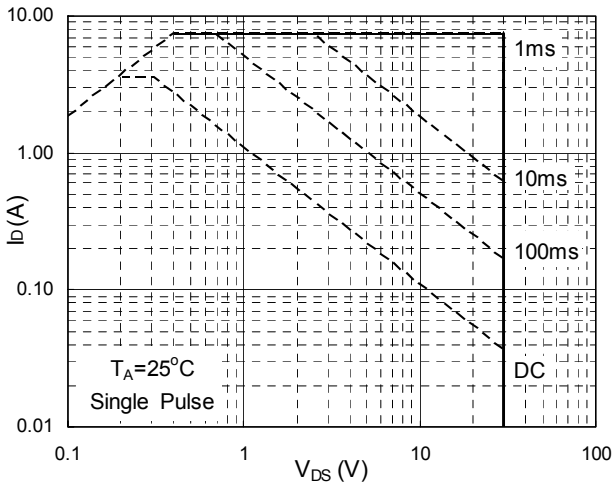


Fig.8 Safe Operating Area

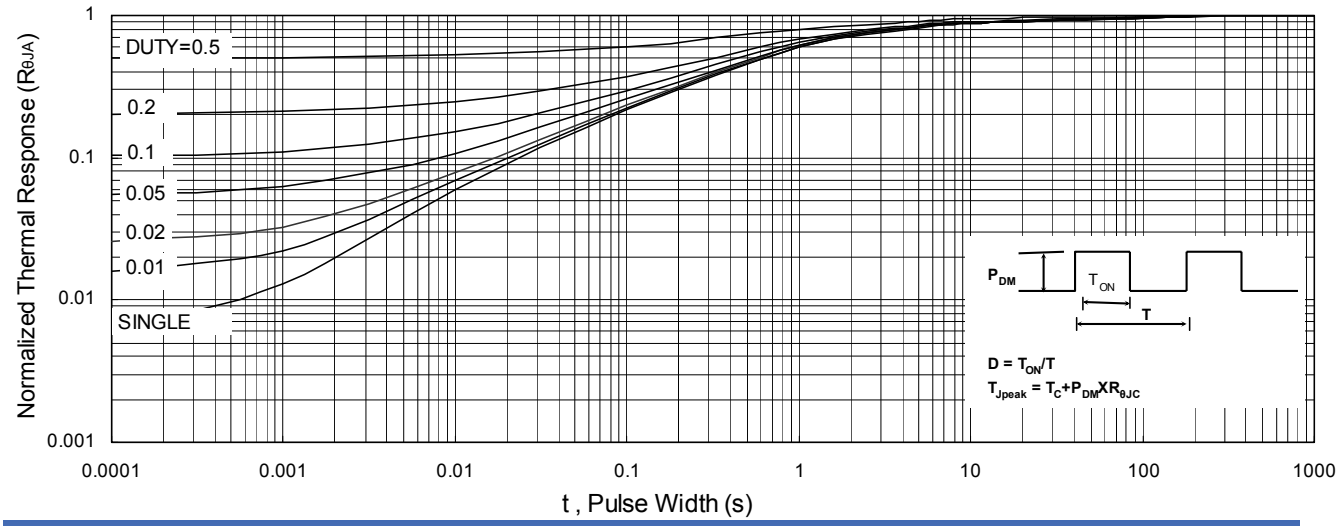


Fig.9 Normalized Maximum Transient Thermal Impedance

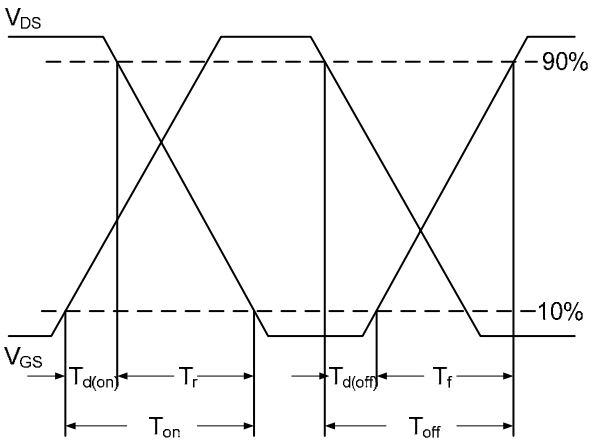


Fig.10 Switching Time Waveform

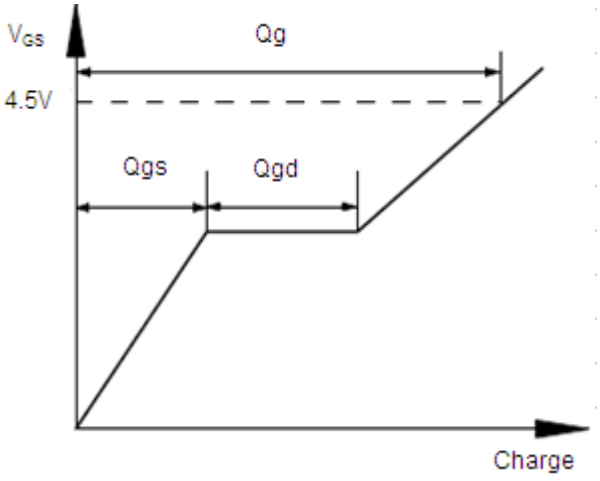


Fig.11 Gate Charge Waveform

N-Channel Typical Characteristics

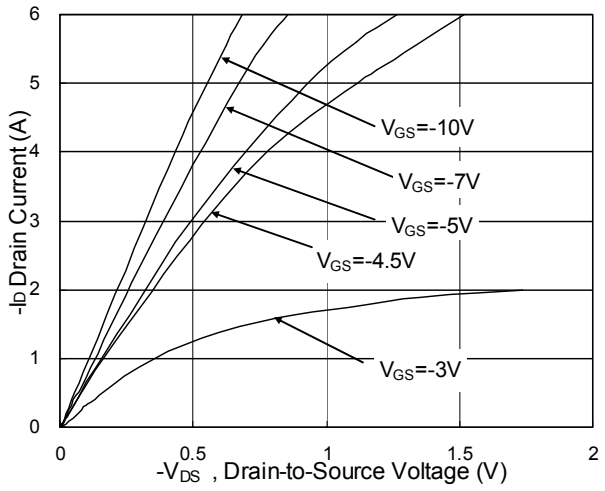


Fig.1 Typical Output Characteristics

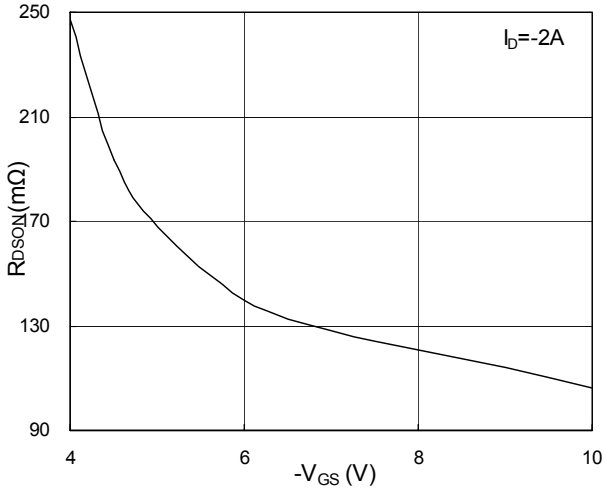


Fig.2 On-Resistance v.s Gate-Source

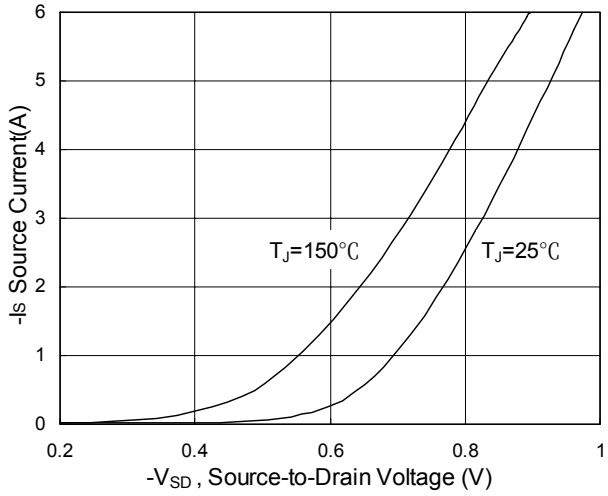


Fig.3 Forward Characteristics of Reverse

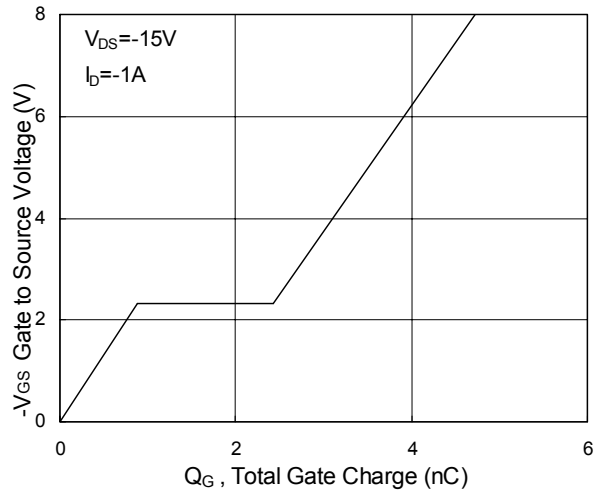


Fig.4 Gate-Charge Characteristics

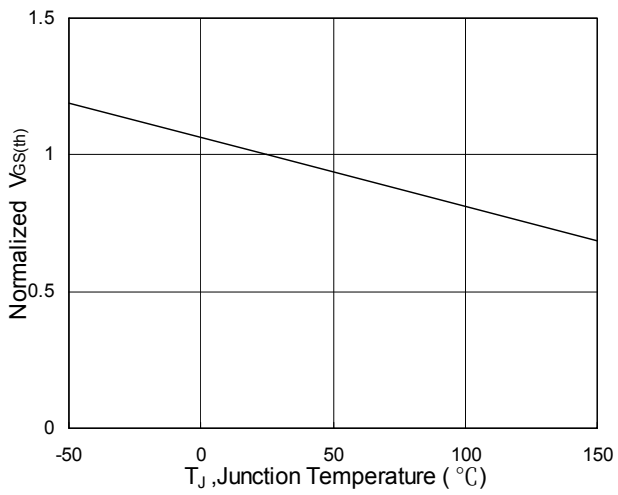


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

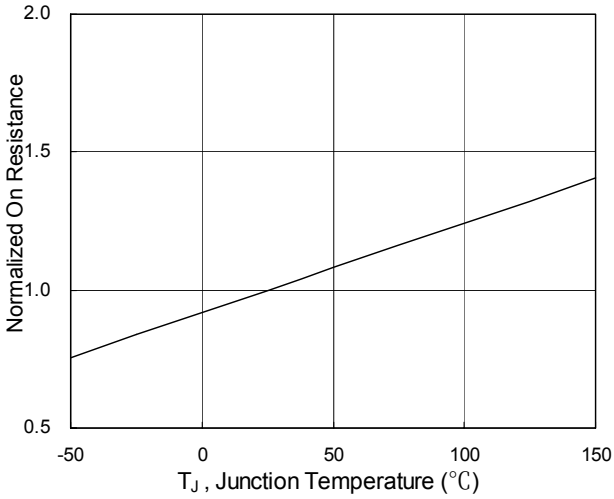


Fig.6 Normalized R_{DSON} v.s T_J

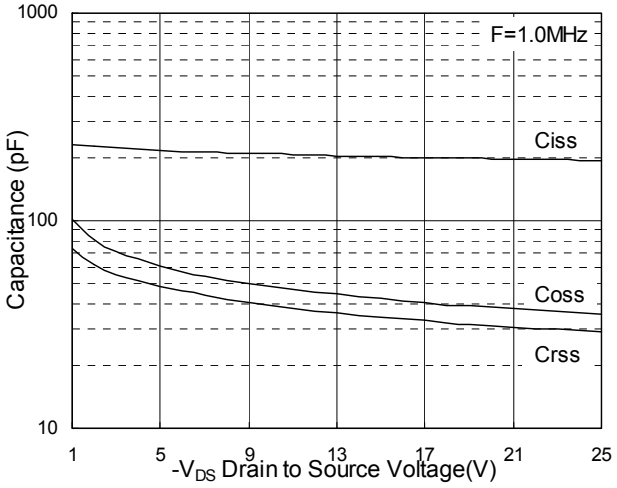


Fig.7 Capacitance

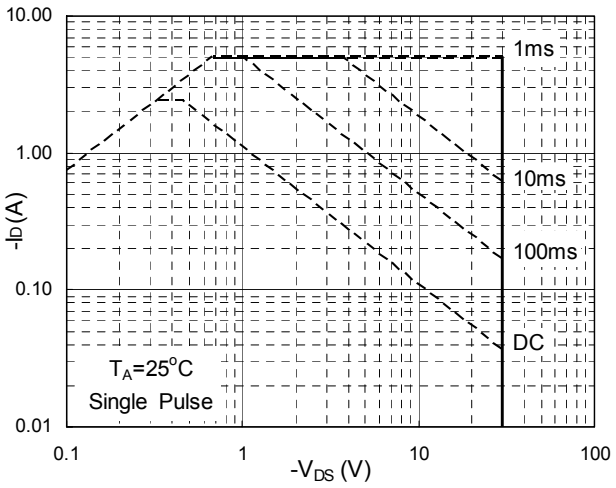


Fig.8 Safe Operating Area

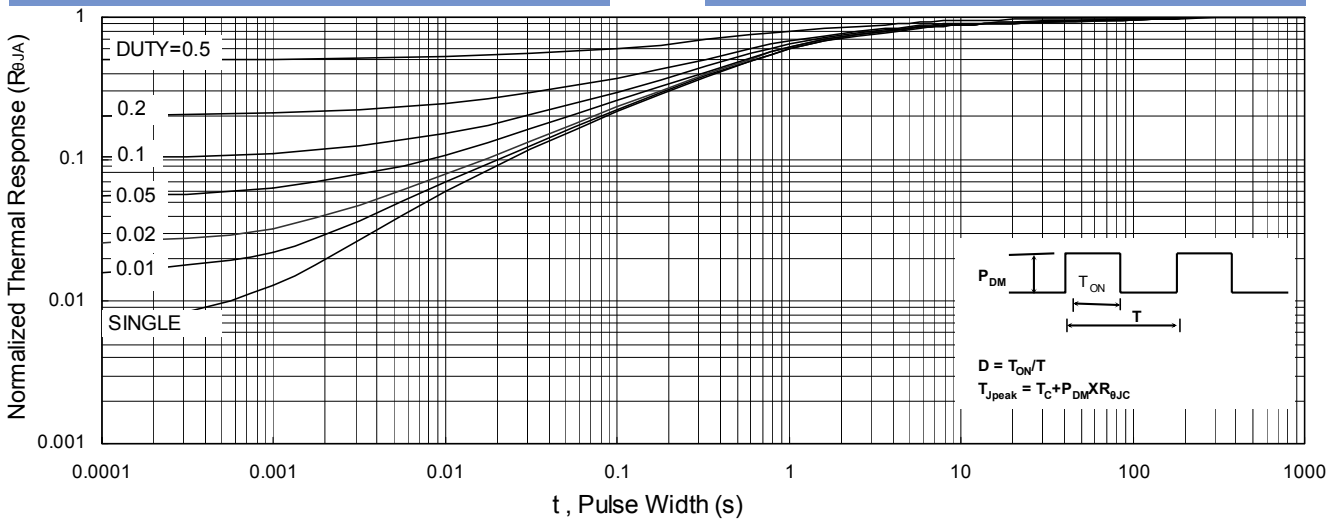


Fig.9 Normalized Maximum Transient Thermal Impedance

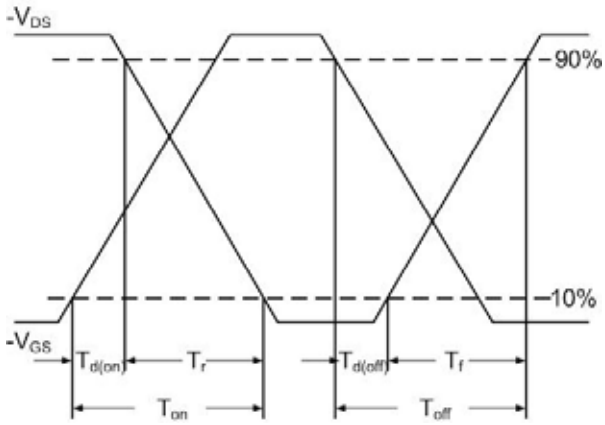


Fig.10 Switching Time Waveform

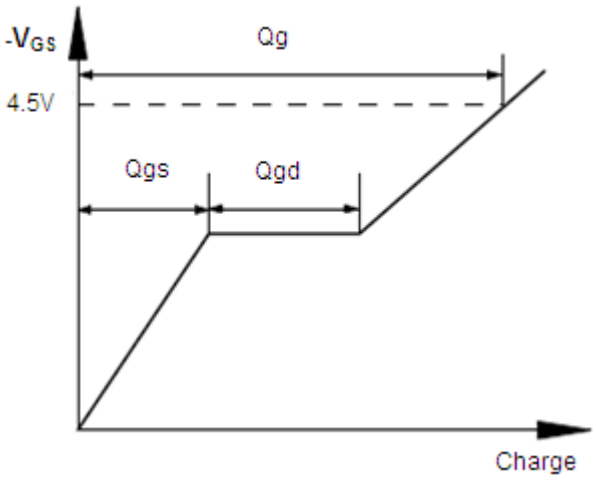
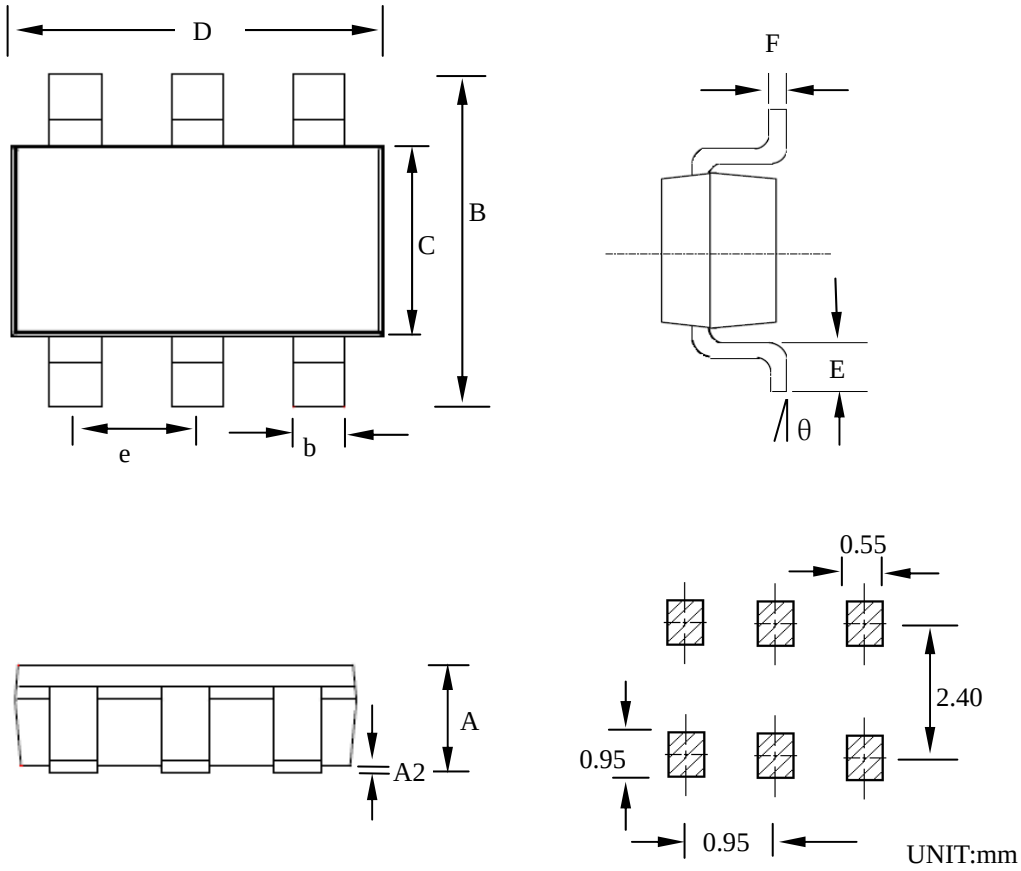
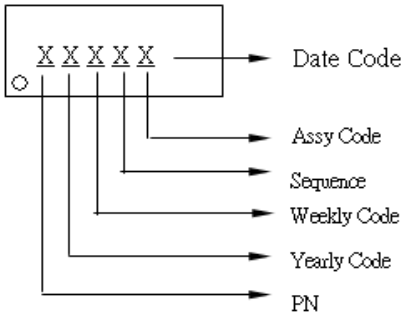


Fig.11 Gate Charge Waveform



LAND PATTERN RECOMMENDATION

MARKING

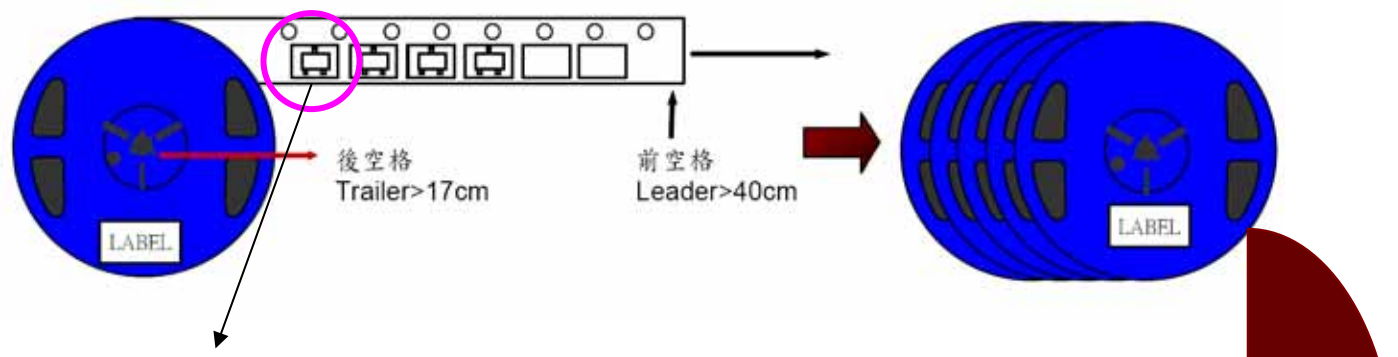


SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
A2	0.00	--	0.10	0.000	--	0.004
B	2.60	2.80	3.00	0.102	0.110	0.118
C	1.40	1.60	1.80	0.055	0.063	0.071
D	2.70	2.90	3.10	0.106	0.114	0.122
E	0.30	0.40	0.60	0.012	0.016	0.024
F	0.07	0.127	0.20	0.003	0.005	0.008
b	0.30	0.40	0.50	0.012	0.016	0.020
e	--	0.95	--	--	0.037	--
θ	0°	5°	10°	0°	5°	10°

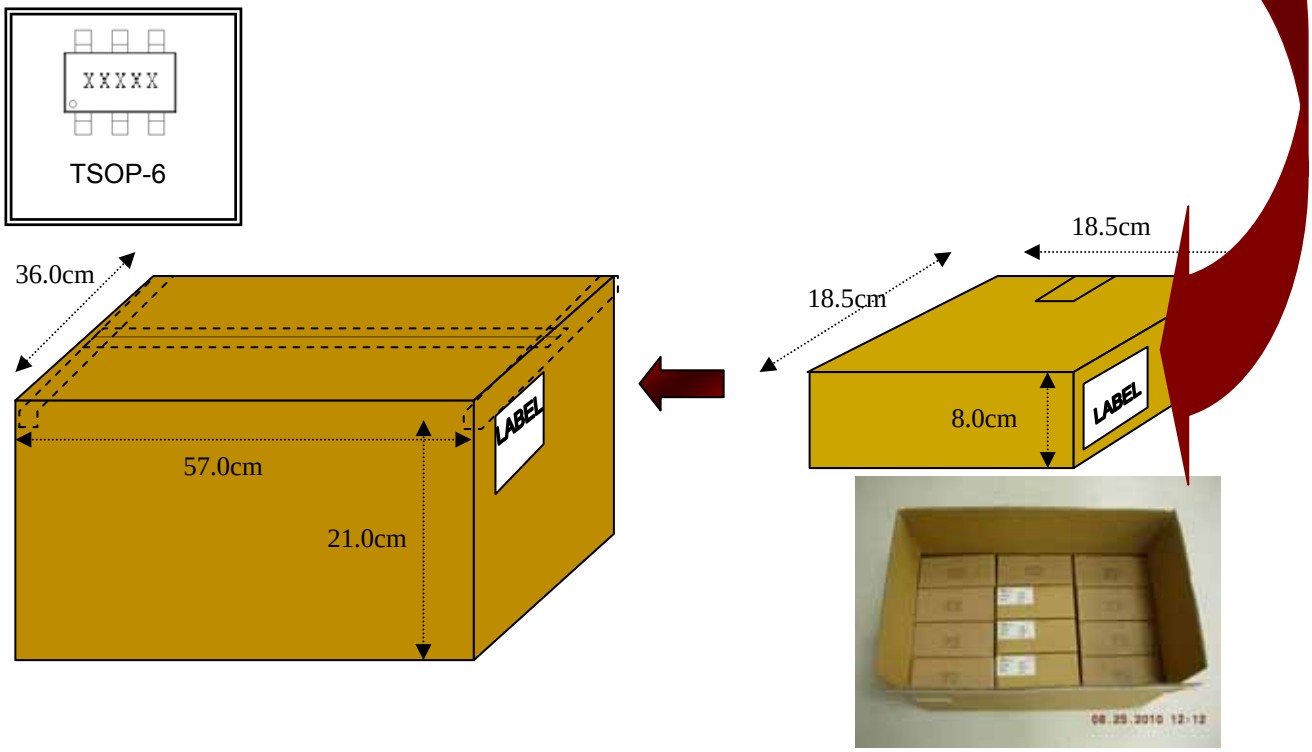
Note:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. CONTROLLING DIMENSION IS MILLIMETER CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACTLY.

Tape & Reel 繞捲及裝箱方式 – TSOP-6



產品正印及方向 –（正印為正時，Tape 圓孔在上方）



封裝形態 PKG TYPE	一 般 包 裝		
	一卷數量 Immediate Quantity	中箱數量 Intermediate Quantity	外箱裝置/數量 Carton Quantity
TSOP-6	3000pcs	15000pcs	180 K
	Reel（7”）	Box(5 reels)	Carton(12 Box)